

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

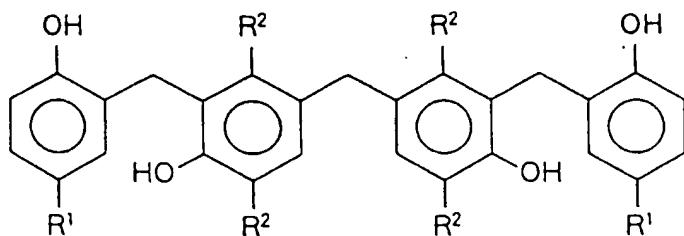
**LISTING OF CLAIMS:**

Claims 1-16 (canceled).

17. (previously presented): A positive photoresist composition comprising

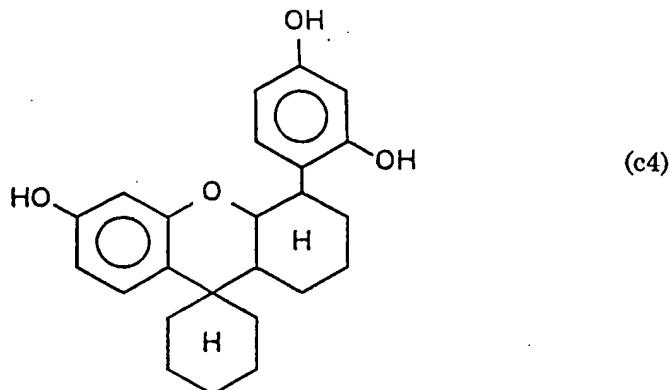
(A) an alkali soluble resin,

(B) a photosensitizer containing quinonediazide ester of a compound of the following formula (I):

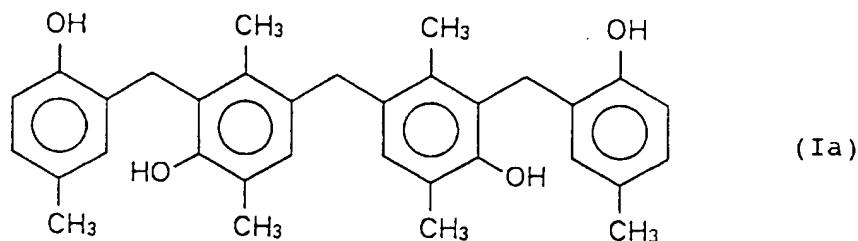


wherein each of R<sup>1</sup> and R<sup>2</sup> is independently a methyl group or an ethyl group, and

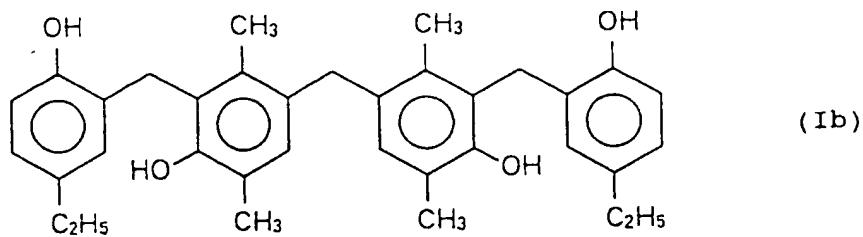
(C) at least one compound of phenol group-containing compounds having structural formula (C4) and having an elution time in the range from 6 to 30 minutes in high performance liquid chromatography, said high performance liquid chromatography being conducted under the following conditions: eluent: a mixed solvent of water:tetrahydrofuran:methanol = 40:24:36 (by weight); column: 4.6 mm (diameter) x 150 mm (length) containing 5 µm silica gel as a filler (carbon content being about 15%); column temperature: 45.0°C; and supply rate of eluent: 0.700 ml/min.



18. (previously presented): The composition according to claim 17, wherein said compound represented by the formula (I) is a compound of the following formula (Ia):



19. (previously presented): The composition according to claim 17, wherein said compound represented by the formula (I) is a compound of the following formula (Ib):



20. (previously presented): A process for forming a resist pattern comprising the steps of:

- (1) coating the positive photoresist composition of claim 17 onto a substrate having a diameter ranged from 8 to 12 inches, and drying the coated substrate to form a resist film,
- (2) subjecting said resist film to selective exposure through a mask,
- (3) heating said resist film, and
- (4) removing the resist film at exposed positions by an aqueous alkali solution.